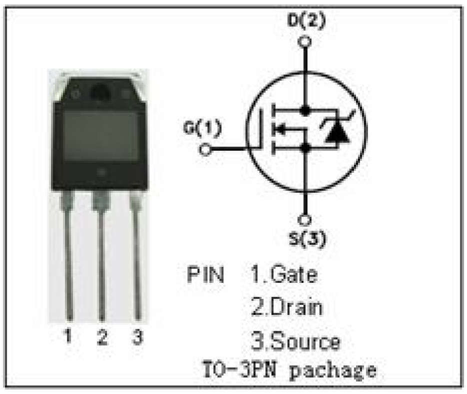
isc N-Channel MOSFET Transistor 25N40

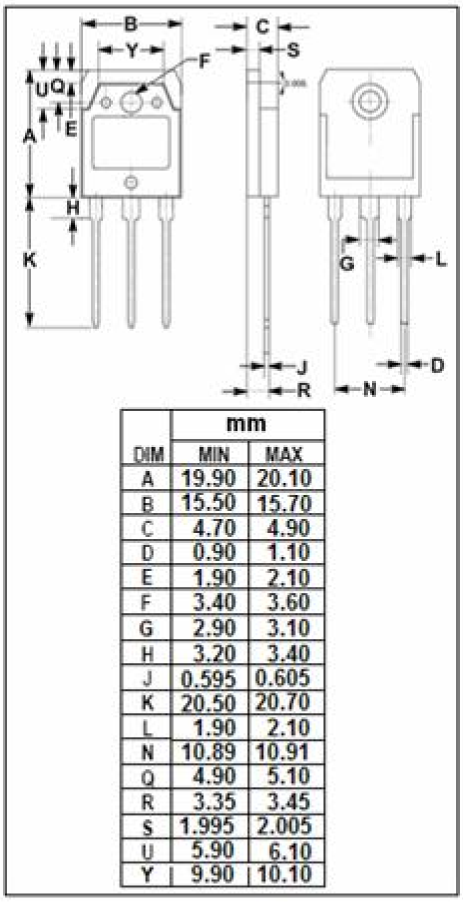
- **FEATURES**
- Drain Current I_D= 25A@ T_C=25℃
- Drain Source Voltage
  : V_{DSS}= 400V(Min)
- Static Drain-Source On-Resistance
  : $R_{DS(on)}$ = 0.2Ω(Max)
- Fast Switching



- **APPLICATIONS**
- Switch mode power supply.

- **ABSOLUTE MAXIMUM RATINGS(T_a=25℃)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	400	V
V_{GS}	Gate-Source Voltage-Continuous	±30	V
I_D	Drain Current-Continuous	25	A
P_D	Total Dissipation @T_C=25℃	278	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.10
H	3.20	3.40
J	0.595	0.605
K	20.50	20.70
L	1.90	2.10
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

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• ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D=250μA	400			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GE}; I_D=250μA	2.0		4.0	V
V_{SD}	Diode Forward On-voltage	I_S= 25A ;V_{GS}= 0			1.5	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D= 12.5A			0.2	Ω
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±30V;V_{DS}= 0			±10	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=400V; V_{GS}= 0			1	μA
C_{iss}	Input Capacitance	V_{DS}=25V; V_{GS}=0V; f_T=1MHz		2400		pF
C_{rss}	Reverse Transfer capacitance			30		
C_{oss}	Output Capacitance			390		
t_r	Rise Time	V_{GS}=10V; I_D=26A; V_{DD}=200V; R_G=25Ω		100		ns
$t_{d(on)}$	Turn-on Delay Time			45		
t_f	Fall Time			66		
$t_{d(off)}$	Turn-off Delay Time			115		